

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re U.S. Patent Application of)
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SAKATA et al.)
)
Application Number: To be Assigned)
)
Filed: Concurrently Herewith)
)
For: SEMICONDUCTOR DEVICE)
)
ATTORNEY DOCKET NO. NITT.0173)

**Honorable Assistant Commissioner
for Patents
Washington, D.C. 20231**

INFORMATION DISCLOSURE STATEMENT

Sir:

Pursuant to 37 C.F.R. §§ 1.56 and 1.97, this Information Disclosure Statement is submitted in the above-identified patent application. A listing of documents to be published on the face of any patent granted from this application is submitted herewith on Form PTO-1449. Any other documents or information submitted for consideration by the Examiner are listed in this paper. A copy of each U.S. and foreign patent, or each publication or portion thereof listed or herein identified, submitted herewith.

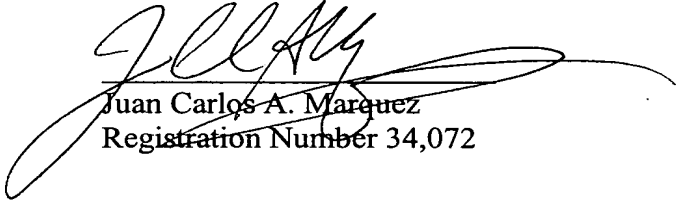
This Information Disclosure Statement is submitted with the initial filing of the application. Accordingly, no fee is due or payable at this time.

The Examiner is requested to acknowledge consideration of the information provided in this paper in accordance with prescribed procedures.

Please charge any additional fees or credit any overpayments in connection with this paper to Deposit Account No. 08-1480.

Respectfully submitted,

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	APPLICANT KAMIYAMA et al.	
	FILING DATE Concurrently Herewith	GROUP

U.S. Patent Documents

Examiner Initial		DOCUMENT NUMBER	DATE	NAME	CLA SS	SUBC LASS	FILING DATE

Foreign Patent Documents

Examiner Initial		DOCUMENT NUMBER	FILING DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION	
							YES	NO

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

		Manzur Gill, Tyler Lowrey and John Park, "Ovonic Unified Memory – A High-Performance Nonvolatile Memory Technology for Stand-Alone Memory and Embedded Applications", 2002 IEEE International Solid-State Circuits Conference, Digest of Technical Papers, 3 pages
		A. Pirovano, A.L. Lacaita, D. Merlani, A. Benvenuti, F. Pellizzer and R. Bez, "Electronic Switching Effect in Phase-Change Memory Cells", 2002 IEEE International Electron Devices Meeting, Technical Digest, pp. 923-926
		Y.N. Hwang et al., "Completely CMOS-Compatible Phase-Change Nonvolatile RAM Using NMOS Cell Transistors", 2003 Non-Volatile Semiconductor Memory Workshop, Digest of Technical Papers, pp. 91-92

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

*This abstract corresponds to Japanese Patent 3127220 above

**The English abstract of this document is Japanese Publication 10-246764 above

PTO1449